

DualCool™ N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16325Q5C

FEATURES

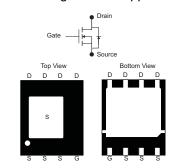
- DualCool™ Package SON 5×6mm
- Optimized for 2-Sided Cooling
- Optimized for 5V Gate Drive
- Ultralow Q_q and Q_{qd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant and Halogen Free

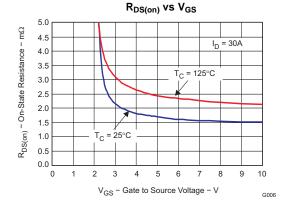
APPLICATIONS

- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.





PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	25	V	
Q_g	Gate Charge Total (4.5V)	18		nC
Q_{gd}	Gate Charge Gate to Drain	3.5		nC
		$V_{GS} = 3V$	2.1	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$	1.7	mΩ
		$V_{GS} = 8V$	1.5	mΩ
V _{GS(th)}	Threshold Voltage	1.1		V

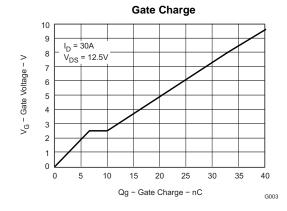
ORDERING INFORMATION

Device	Package		Device Package Media		Qty	Ship
CSD16325Q5C	SON 5×6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel		

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT						
V_{DS}	Drain to Source Voltage	25	٧						
V_{GS}	Gate to Source Voltage	+10 / -8	V						
	Continuous Drain Current, T _C = 25°C	100	Α						
I _D	Continuous Drain Current ⁽¹⁾	33	Α						
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	200	Α						
P_D	Power Dissipation ⁽¹⁾	3.1	W						
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C						
E _{AS}	Avalanche Energy, single pulse $I_D = 100A$, $L = 0.1mH$, $R_G = 25\Omega$	500	mJ						

- (1) Typical $R_{\theta JA} = 38^{\circ} \text{C/W}$ on 1-in ^2 Cu, (2-oz.) on a 0.060" thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Static C	haracteristics				
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25		V
I _{DSS}	Drain to Source Leakage	V _{GS} = 0V, V _{DS} = 20V		1	μΑ
I _{GSS}	Gate to Source Leakage	$V_{DS} = 0V, V_{GS} = +10/-8V$		100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9 1.1	1.4	V
		$V_{GS} = 3V$, $I_D = 30A$	2.1	2.9	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 30A$	1.7	2.2	mΩ
		$V_{GS} = 8V, I_D = 30A$	1.5	2	mΩ
9 _{fs}	Transconductance	$V_{DS} = 15V, I_D = 30A$	159		S
Dynami	c Characteristics	·			
C _{iss}	Input Capacitance		3070	4000	pF
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ $f = 1MHz$	2190	2850	pF
C_{rss}	Reverse Transfer Capacitance	· ·····- <u>-</u>	120	150	pF
R_{G}	Series Gate Resistance		1.6	3.2	Ω
Q_g	Gate Charge Total (4.5V)		18	25	nC
Q_{gd}	Gate Charge – Gate to Drain	$V_{DS} = 12.5V$,	3.5		nC
Q_{gs}	Gate Charge – Gate to Source	$I_{DS} = 30A$	6.6		nC
$Q_{g(th)}$	Gate Charge at Vth		3.1		nC
Q _{oss}	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$	43		nC
$t_{d(on)}$	Turn On Delay Time		10.5		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$	16		ns
$t_{d(off)}$	Turn Off Delay Time	$I_{DS} = 30A$, $R_G = 2\Omega$	32		ns
t _f	Fall Time		12		ns
Diode C	haracteristics			· —	
V_{SD}	Diode Forward Voltage	$I_{DS} = 30A, V_{GS} = 0V$	0.8	1	>
Q_{rr}	Reverse Recovery Charge	V _{DD} = 13V, I _F = 30A, di/dt = 300A/μs	63		nC
t _{rr}	Reverse Recovery Time	$v_{DD} = 13v$, $i_F = 30A$, $ui/ui = 300A/\mu S$	47		ns

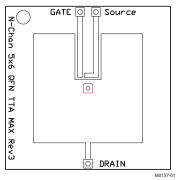
THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

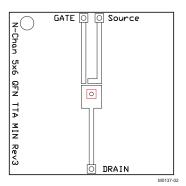
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case (Top Source) ⁽¹⁾			1.4	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case (Bottom drain) ⁽¹⁾			1	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			50	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² 2-oz. Cu pad on a 1.5 × 1.5-inch 0.060-inch thick FR4 board. $R_{\theta JC}$ is specified by design, whereas $R_{\theta CA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² of 2-oz. Cu.





Max $R_{\theta JA} = 50$ °C/W when mounted on 1 inch² of 2-oz. Cu.



Max $R_{\theta JA} = 126^{\circ}C/W$ when mounted on minimum pad area of 2-oz.Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

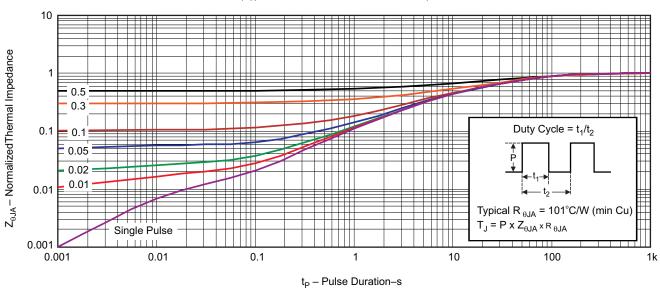


Figure 1. Transient Thermal Impedance

G012



TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

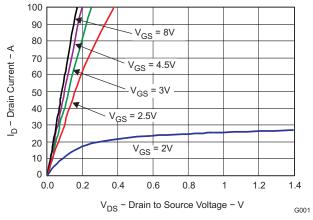


Figure 2. Saturation Characteristics

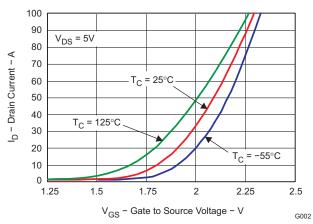


Figure 3. Transfer Characteristics

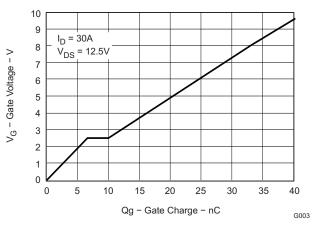


Figure 4. Gate Charge

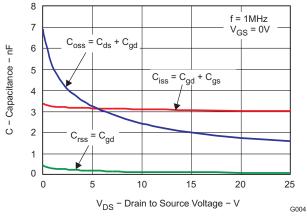


Figure 5. Capacitance

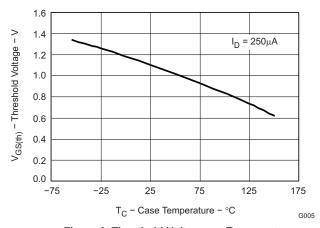


Figure 6. Threshold Voltage vs. Temperature

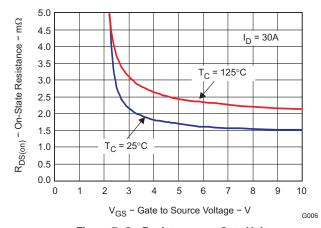


Figure 7. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

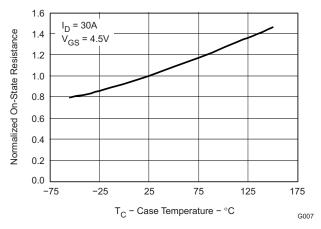


Figure 8. On Resistance vs. Temperature

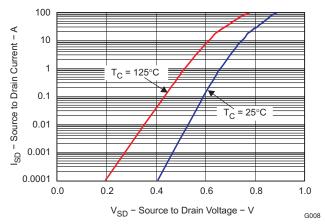


Figure 9. Typical Diode Forward Voltage

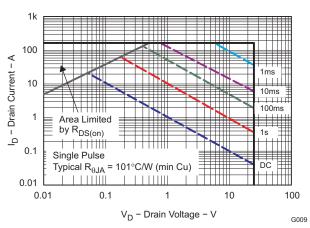


Figure 10. Maximum Safe Operating Area

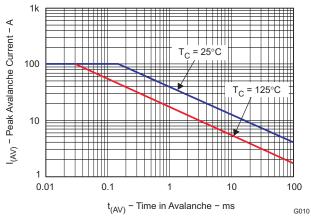


Figure 11. Single Pulse Unclamped Inductive Switching

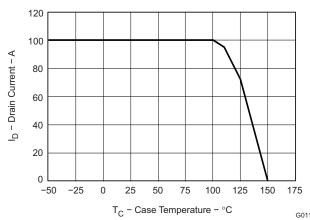
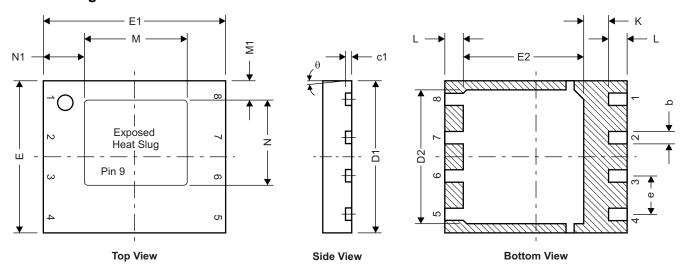


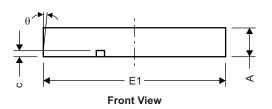
Figure 12. Maximum Drain Current vs. Temperature



MECHANICAL DATA

Q5C Package Dimensions



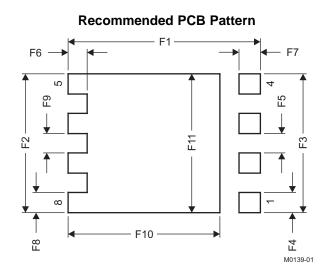


DualCool™Pinout				
Pin#	Label			
1, 2, 3, 9	Source			
4	Gate			
5, 6, 7, 8	Drain			

M0162-01

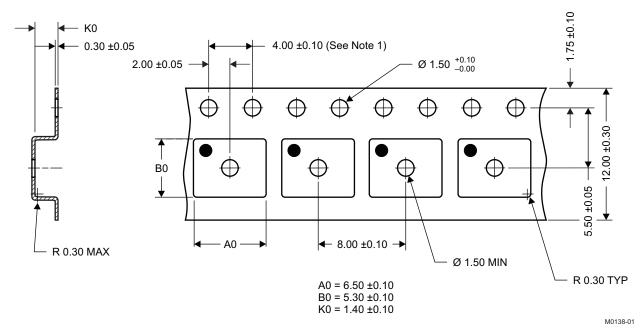
DIM	MILLIM	ETERS	INCHES			
DIW	MIN	MAX	MIN	MAX		
Α	0.950	1.050	0.037	0.039		
b	0.360	0.460	0.014	0.018		
С	0.150	0.250	0.006	0.010		
c1	0.150	0.250	0.006	0.010		
D1	4.900	5.100	0.193	0.201		
D2	4.320	4.520	0.170	0.178		
E	4.900	5.100	0.193	0.201		
E1	5.900	6.100	0.232	0.240		
E2	3.920	4.12	0.154	0.162		
е	1.27	TYP	0.050			
L	0.510	0.710	0.020	0.028		
θ	-	_	_	_		
K	0.760	_	0.030	_		
М	3.260	3.460	0.128	0.136		
M1	0.520	0.720	0.020	0.028		
N	2.720	2.920	0.107	0.115		
N1	1.227	1.427	0.048	0.056		





DIM	MILLIN	IETERS	INCHES		
DIN	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.46	4.56	0.176	0.18	
F3	4.46	4.56	0.176	0.18	
F4	0.65	0.7	0.026	0.028	
F5	0.62	0.67	0.024	0.026	
F6	0.63	0.68	0.025	0.027	
F7	0.7	0.8	0.028	0.031	
F8	0.65	0.7	0.026	0.028	
F9	0.62	0.67	0.024	0.026	
F10	4.9	5	0.193	0.197	
F11	4.46	4.56	0.176	0.18	

Q5C Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible



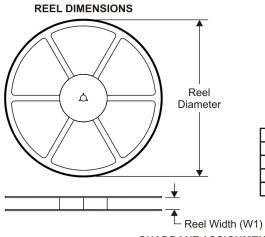
REVISION HISTORY

Changes from Original (December 2009) to Revision A				
Changed the labels on the Bottom View pinout image	1			
Changed the Mechanical Data dimensions table. Added dimensions for M, M1, N and N1	6			
Changes from Revision A (April 2010) to Revision B	Page			
• Changed $R_{DS(on)}$ - V_{GS} = 3V in the Electrical Characteristics table From: 2.7 To: 2.9 in the max	column 2			
Deleted the Package Marking Information section	7			

PACKAGE MATERIALS INFORMATION

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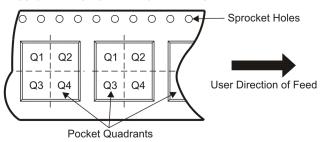
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16325Q5C	SON	DQU	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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*All dimensions are nominal

ĺ	Device	Device Package Type		Package Drawing Pins		Length (mm)	Width (mm)	Height (mm)	
	CSD16325Q5C	SON	DQU	8	2500	335.0	335.0	32.0	

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